

**SEMICONDUCTOR DEVICE INCLUDING SEMICONDUCTOR MEMORY
ELEMENT AND METHOD FOR PRODUCING SAME**

5 Abstract of the Disclosure

A wafer, in which a plurality of rectangular regions are defined on the face of the wafer by streets arranged in a lattice pattern, and a semiconductor memory element is
10 disposed in each of the rectangular regions, is divided along the streets to separate the rectangular regions individually, thereby forming a plurality of semiconductor devices. Before the wafer is divided along the streets, a strained layer having a thickness of 0.20 μm or less,
15 especially 0.05 to 0.20 μm , is formed in the back of the wafer. The strained layer is formed by grinding the back of the semiconductor wafer by a grinding member formed by bonding diamond abrasive grains having a grain size of 4 μm or less by a bonding material.

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Figure 2